



STP40NF10

N-channel 100 V, 0.025 Ω , 50 A TO-220
low gate charge STripFET™ II Power MOSFET

Features

Order code	V _{DSS}	R _{DS(on)} max.	I _D
STP40NF10	100 V	< 0.028 Ω	50 A

- Exceptional dv/dt capability
- Low gate charge
- 100% avalanche tested

Application

Switching applications

Description

This N-channel 100 V Power MOSFET is the latest development of STMicroelectronics unique "single feature size" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps allowing remarkable manufacturing reproducibility.

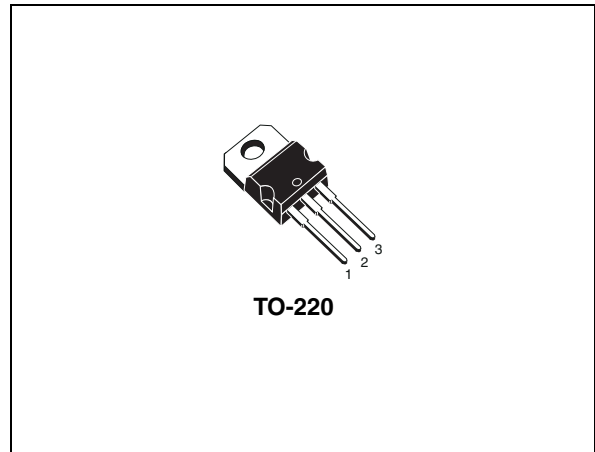


Figure 1. Internal schematic diagram

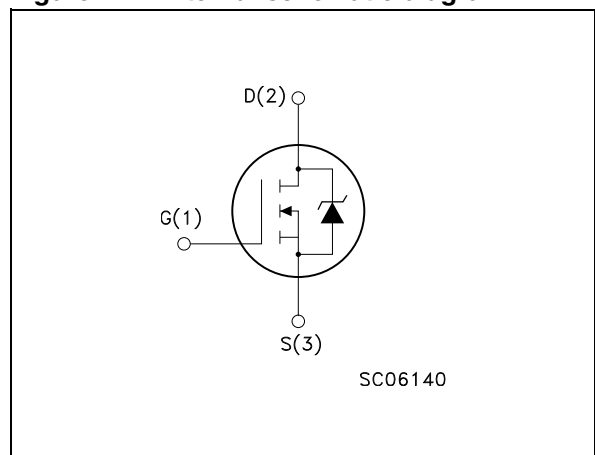


Table 1. Device summary

Order code	Marking	Package	Packaging
STP40NF10	P40NF10@	TO-220	Tube

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage ($V_{GS} = 0$)	100	V
V_{GS}	Gate- source voltage	± 20	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	50	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	35	A
$I_{DM}^{(2)}$	Drain current (pulsed)	200	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	150	W
	Derating factor	1	W/ $^\circ\text{C}$
$dv/dt^{(3)}$	Peak diode recovery voltage slope	27	V/ns
$E_{AS}^{(4)}$	Single pulse avalanche energy	385	mJ
T_{stg}	Storage temperature	- 55 to 175	$^\circ\text{C}$
T_j	Max. operating junction temperature		

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. $I_{SD} \leq 50\text{ A}$, $di/dt \leq 600\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.
4. Starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = 50\text{ A}$, $V_{DD} = 25\text{ V}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	1	$^\circ\text{C}/\text{W}$
R_{thj-a}	Thermal resistance junction-ambient max	62.5	$^\circ\text{C}/\text{W}$
T_l	Maximum lead temperature for soldering purpose	300	$^\circ\text{C}$

2 Electrical characteristics

($T_{CASE} = 25\text{ °C}$ unless otherwise specified)

Table 4. On/off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown voltage	$I_D = 250\ \mu A, V_{GS} = 0$	100			V
I_{DSS}	Zero gate voltage Drain current ($V_{GS} = 0$)	$V_{DS} = \text{Max rating}$ $V_{DS} = \text{Max rating}, T_C = 125\text{ °C}$			1 10	μA μA
I_{GSS}	Gate-body leakage current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{ V}$			± 100	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu A$	2	3	4	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10\text{ V}, I_D = 25\text{ A}$		0.025	0.028	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$g_{fs}^{(1)}$	Forward transconductance	$V_{DS} = 15\text{ V}, I_D = 28\text{ A}$	-	22		S
C_{iss}	Input capacitance	$V_{DS} = 25\text{ V}, f = 1\text{ MHz}, V_{GS} = 0$	-	2180		pF
C_{oss}	Output capacitance			298		pF
C_{rss}	Reverse transfer capacitance			83.7		pF
Q_g	Total gate charge	$V_{DD} = 50\text{ V}, I_D = 40\text{ A}, V_{GS} = 10\text{ V}$ <i>(see Figure 15)</i>	-	46.5	62	nC
Q_{gs}	Gate-source charge			13.3		nC
Q_{gd}	Gate-drain charge			17.5	22.5	nC

1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5.

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 50\text{ V}, I_D = 25\text{ A}$ $R_G = 4.7\ \Omega, V_{GS} = 10\text{ V}$ <i>(see Figure 14)</i>	-	21	-	ns
t_r	Rise time			46	-	ns
$t_{d(off)}$	Turn-off-delay time			54	-	ns
t_f	Fall time			13	-	ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max	Unit
I_{SD}	Source-drain current		-		80	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		320	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 50A, V_{GS} = 0$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 50A, V_{DD} = 25V$ $di/dt = 100A/\mu s,$ $T_j = 150^\circ C$ <i>(see Figure 16)</i>	-	80		ns
Q_{rr}	Reverse recovery charge			250		nC
I_{RRM}	Reverse recovery current			6.4		A

1. Pulse width limited by safe operating area.

2. Pulsed: Pulse duration = 300 μs , duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area for TO-220

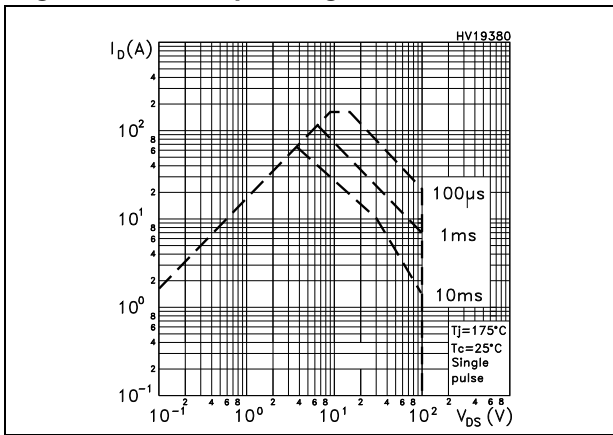


Figure 3. Thermal impedance for TO-220

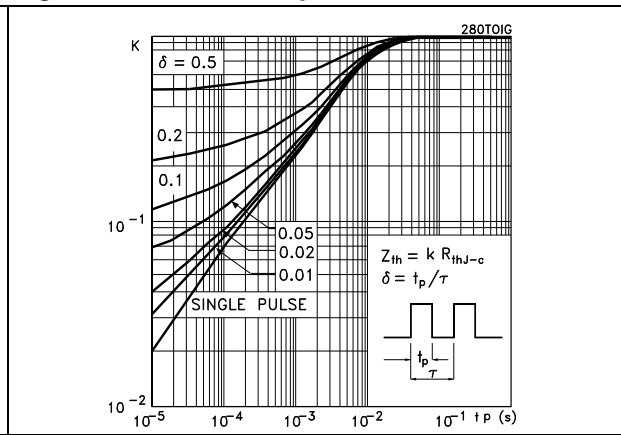


Figure 4. Output characteristics

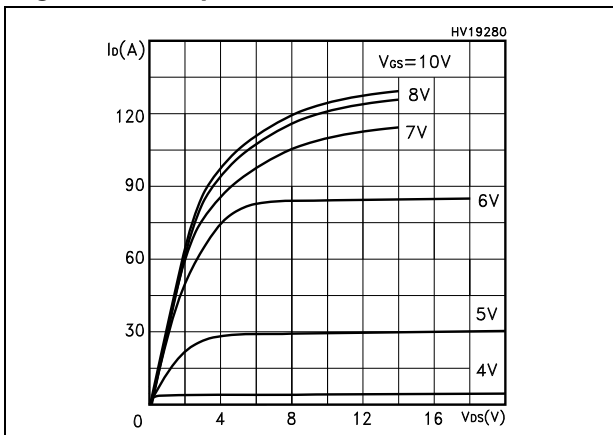


Figure 5. Transfer characteristics

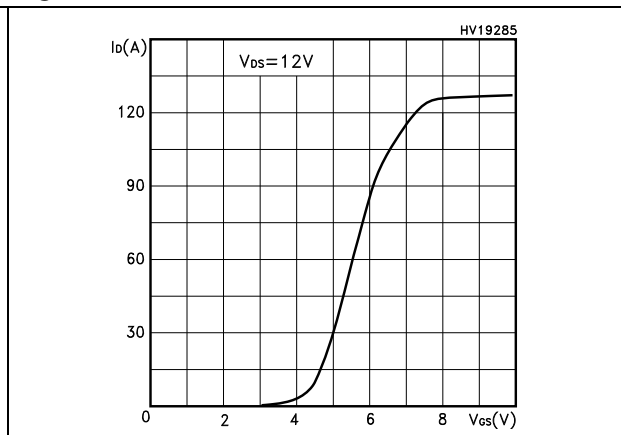


Figure 6. Transconductance

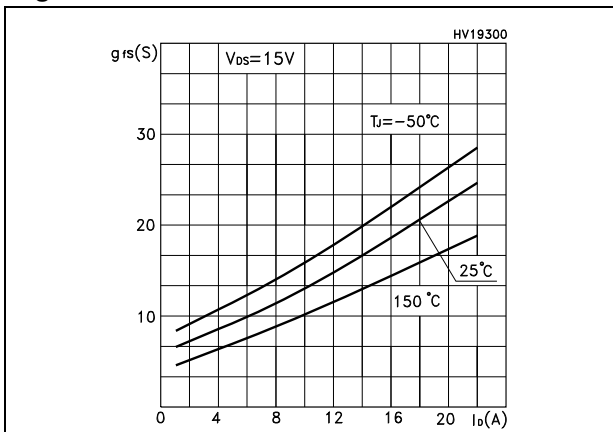


Figure 7. Static drain-source on resistance

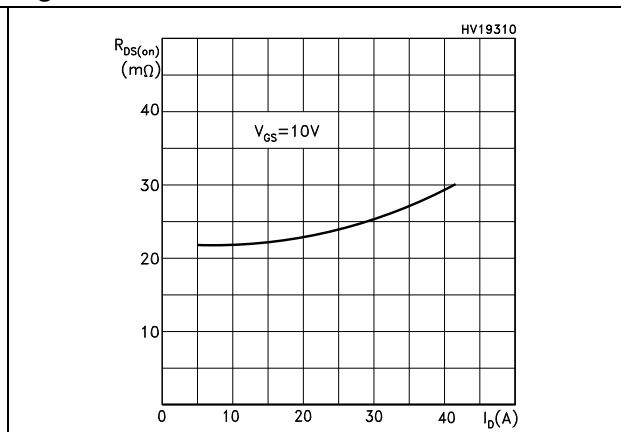


Figure 8. Gate charge vs. gate-source voltage Figure 9. Capacitance variations

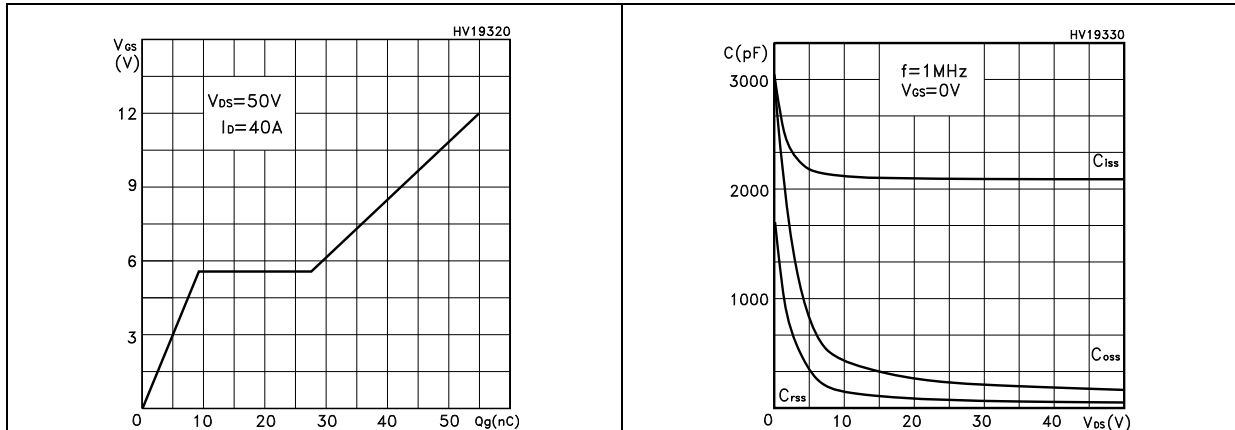


Figure 10. Normalized gate threshold voltage vs. temperature Figure 11. Normalized on resistance vs. temperature

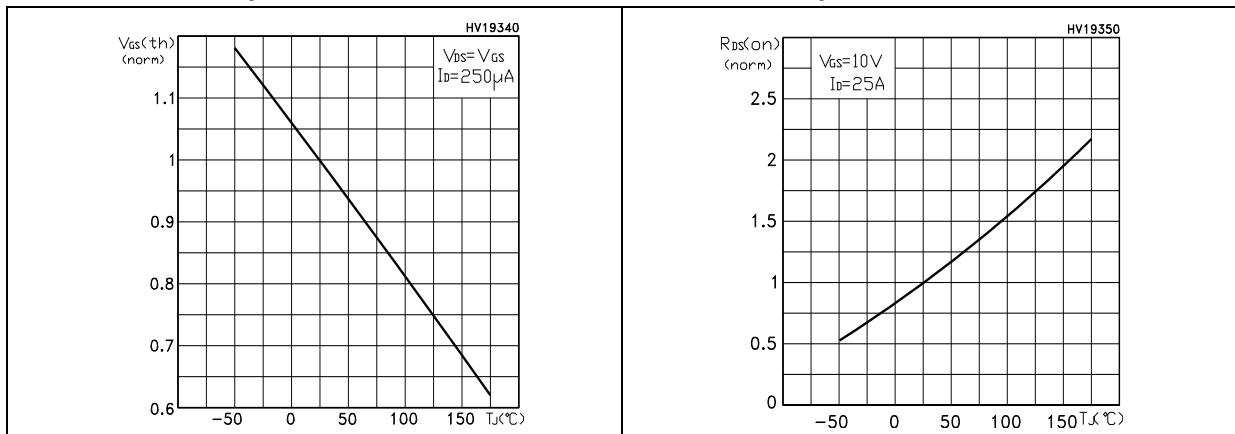
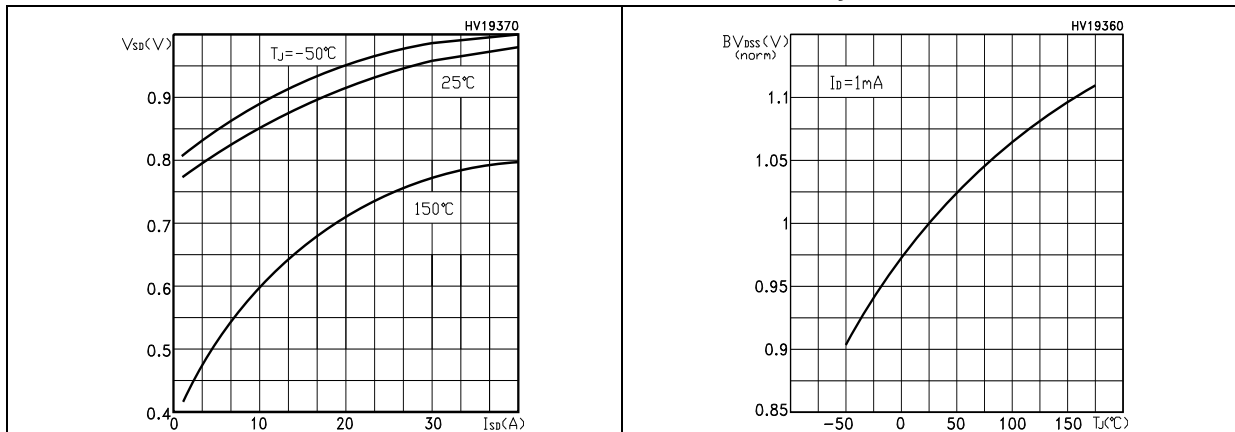


Figure 12. Source-drain diode forward characteristics Figure 13. Normalized breakdown voltage vs. T_j



3 Test circuit

Figure 14. Switching times test circuit for resistive load



Figure 15. Gate charge test circuit



Figure 16. Test circuit for inductive load switching and diode recovery times



Figure 17. Unclamped Inductive load test circuit



Figure 18. Unclamped inductive waveform

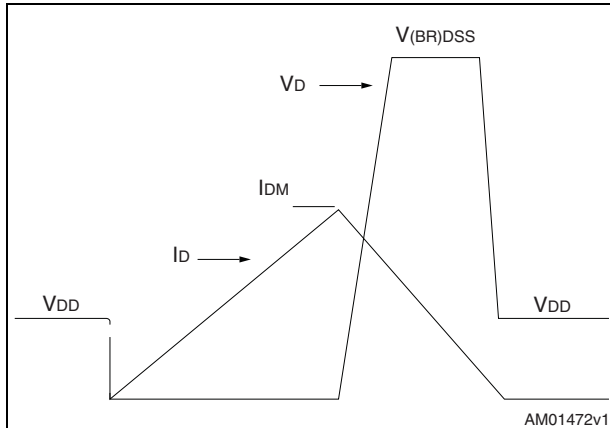
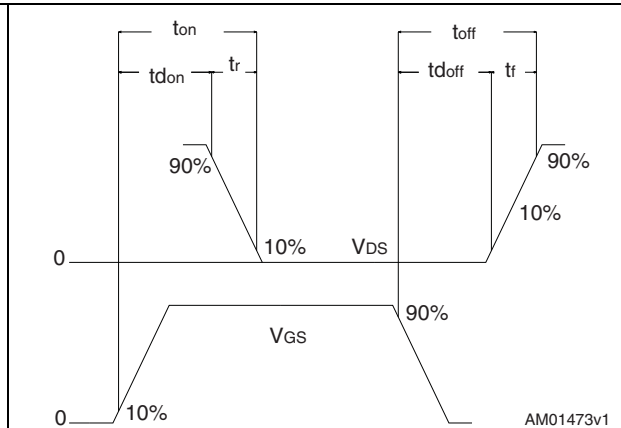


Figure 19. Switching time waveform

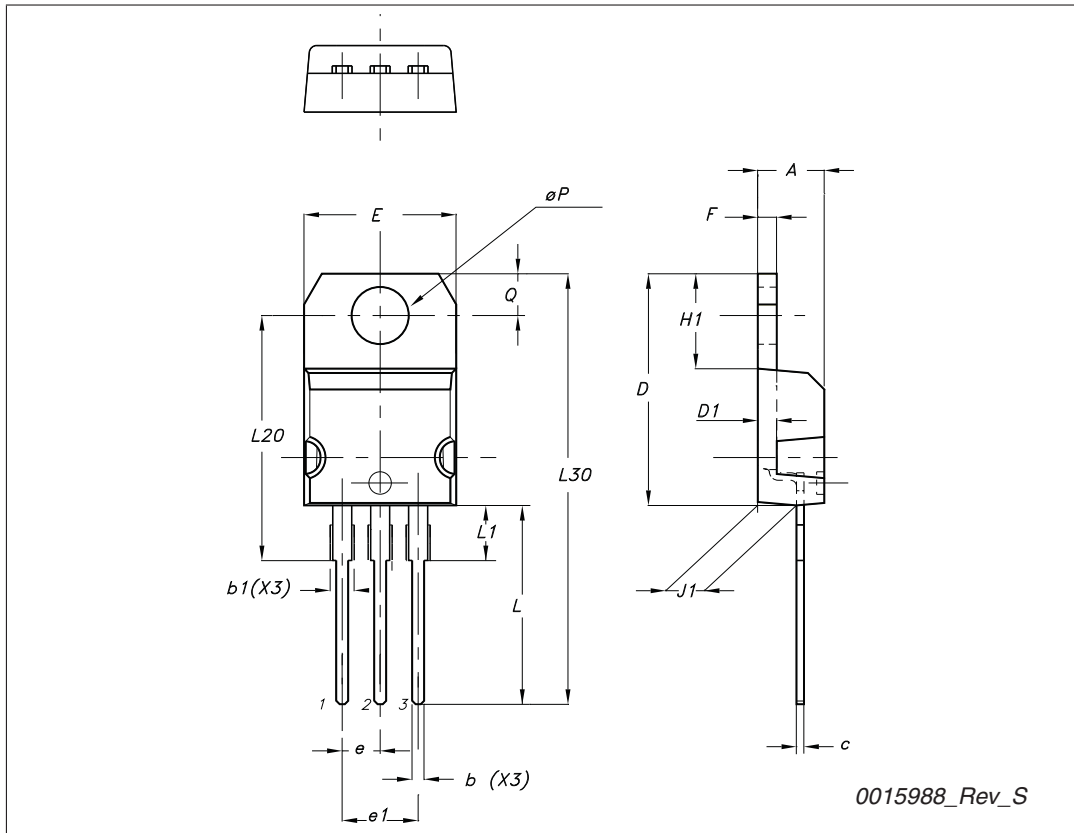


4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
∅P	3.75		3.85
Q	2.65		2.95



5 Revision history

Table 8. Document revision history

Date	Revision	Changes
16-Dec-2004	1	First version.
17-Aug-2006	2	The document has been reformatted.
31-Jan-2007	3	Typo mistake on Table 2 .
19-Sep-2007	4	Added DPAK.
10-Nov-2010	5	Removed DPAK.

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